

Product Overview

NCV57001: IGBT Gate Driver, Isolated High Current and High Efficiency, with Internal Galvanic Isolation

For complete documentation, see the data sheet.

NCV57001 is a high-current single channel IGBT driver with internal galvanic isolation, designed for high system efficiency and reliability in high power applications. Its features include complementary inputs, open drain FAULT and Ready outputs, active Miller clamp, accurate UVLOs, DESAT protection, and soft turn-off at DESAT. NCV57001 accommodates both 5V and 3.3V signals on the input side and wide bias voltage range on the driver side including negative voltage capability. NCV57001 provides > 5 kVrms (UL1577 rating) galvanic isolation and > 1200 Viorm (working voltage) capabilities. NCV57001 is available in the wide-body SOIC-16 package with guaranteed 8 mm creepage distance between input and output to fulfill reinforced safety insulation requirements.

Features

- High Current Output(+4/-6 A) at IGBT Miller Plateau Voltages
- · Short Propagation Delays with Accurate Matching
- · DESAT with Soft Turn Off
- Active Miller Clamp and Negative Gate Voltage
- High Transient & Electromagnetic Immunity
- 5 kV Galvanic Isolation

Applications

- Automotive Power Supplies
- HEV/EV Traction Inverters
- OBC
- **BSG** Inverters
- PTC Heaters

Benefits

- · Improves system efficiency
- · Improves PWM signal integrity
- · Protection against overload and short circuits
- · Prevents spurious gate turn-on
- Ruggedness in fast slew rate high voltage and high current switching applications
- · Galvanic isolation to separate high voltage and low voltage sides to provide safety and protection

End Products

- Automobiles
- xEV/EV Automobiles

Part Electrical Specifications														
Product	Pricing (\$/Unit)	Compliance	Status	Power Switch	Numbe r of Output s	Topolo gy	Isolatio n Type	V _{in} Max (V)	V _{cc} Max (V)	Drive Source /Sink Typ (mA)	Rise Time (ns)	Fall Time (ns)	t _p Max (ns)	Packag e Type
NCV57001DWR2G		AEC Qualified PPAP Capable Pb-free Halide free	Active	IGBT SiC MOS FET	1	Single	Galvan ic Isolatio n	5.5	24	6000 / 6000	10	15	90	SOIC- 16W

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